

Multiemitter cavity quantum electrodynamics in 4H-silicon carbide-on-insulator photonics

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Abstract: We demonstrate small-ensemble ($N \sim 10$ emitters) cavity quantum electrodynamics with silicon vacancy color centers in microresonators using the 4H-Silicon Carbide on Insulator photonics platform. © 2023 The Author(s)

Solid-state cavity quantum electrodynamics (CQED) systems, such as cavity-coupled quantum dots [1,2], color centers in diamond [3–5] and silicon carbide [6], and rare-earth ions [7], have enabled the studies of cavity-coupled emitters in both microscopic and macroscopic regimes. Experimentally-realized microscopic systems such as single- and two-emitter CQED devices [1–4,6,7], owing to their low dimensionality, can be solved exactly. Macroscopic systems, where large ensembles ($\sim 10^6$ emitters) are coupled to a cavity [8], can be analyzed with semiclassical approximations. The intermediate — mesoscopic — regime has not yet been experimentally realized in the solid-state.

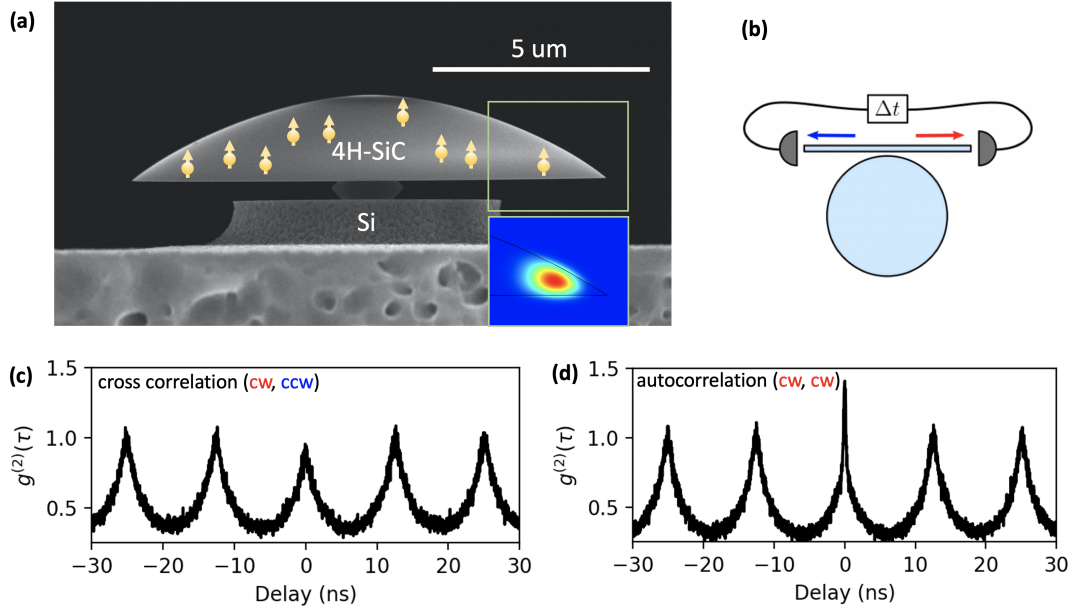


Fig. 1. (a) Scanning electron micrograph (SEM) of the SiC-on-insulator resonator. Inset shows the field profile of the transverse-magnetic (TM) whispering gallery mode. The TM mode couples optically to the V_{Si} emitter ensemble. (b) Clockwise and counterclockwise emission from the resonator can be independently analyzed via single photon detectors. (c) Second-order photon cross-correlation measurement of the ensemble emission. Correlating clockwise and counterclockwise photon statistics results in a quasi-distinguishable statistics, with $g^{(2)}(0) = 0.9$. (d) autocorrelation on the clockwise emission reveals superradiant emission, evidenced by $g^{(2)}(0)$ exceeding unity.

Here, using silicon vacancy (V_{Si}) color centers in silicon carbide coupled to a photonic resonator, we demonstrate the superradiant emission of a small ($N \sim 10$) ensemble of emitters in a cavity. The device fabrication is performed as follows: a 20 μm n-doped (nitrogen concentration $2 \cdot 10^{13} \text{ cm}^{-3}$) SiC epilayer is grown via chemical

vapor deposition on an n-type (0001) 4H-SiC substrate. The sample is irradiated with 2 MeV electrons with a fluence of $3.5 \cdot 10^{14} \text{ cm}^{-2}$ to generate V_{Si} defects. The 4H-SiC-on-insulator material stack is produced via grinding and polishing [9, 10]. A photoresist reflow process [11] is used to fabricate the photonic resonators with low surface roughness as follows: Photoresist (S1822, Shipley) is patterned using direct write lithography, followed by post-development bake (30 seconds at 135°C) to induce photoresist reflow. Then, the pattern is transferred into SiC via a reactive ion etch (SF_6 gas, Oxford Plasmalab 100). The resonators are undercut via a wet hydrofluoric acid etch and a gas XeF_2 etch. A side-view of a completed device is shown in Fig. 1(a).

Experiments are performed in a 4 K closed-cycle cryostat (Montana Instruments). Coupling to the resonator is achieved via a tapered fiber. Cryogenic argon gas condensation is used to tune the microdisk on-resonance with the emitter ensemble. The above-resonant excitation of the emitter ensemble is performed using a 80 MHz repetition rate femtosecond pulsed laser (wavelength 740 nm). The emission is filtered with a home-built monochromator with a 20 GHz bandwidth. By correlating photon emission into opposite directions inside the resonator (correlating clockwise emission and counterclockwise emission), we can observe quasi-distinguishable emission behavior for randomly-placed emitters [6] (Fig. 1(c)), allowing us to estimate the effective number of emitters from the $g^{(2)}(0)$ value to be $N_{\text{eff}} = 10$. In contrast, performing the photon autocorrelation on a single emission direction reveals superradiant bunching (Fig. 1(d)), indicating indistinguishable emission of the ensemble of emitters.

This demonstration is a step towards investigating mesoscopic disordered multi-emitter systems. Furthermore, combined with integrated spectral control of individual emitters via dc Stark shift [12], the demonstrated device architecture may enable the engineering of controllable multi-emitter interactions.

Acknowledgements

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References

1. T. Yoshie, A. Scherer, J. Hendrickson, G. Khitrova, H. Gibbs, G. Rupper, C. Ell, O. Shchekin, and D. Deppe, "Vacuum rabi splitting with a single quantum dot in a photonic crystal nanocavity," *Nature* **432**, 200–203 (2004).
2. I. Fushman, D. Englund, A. Faraon, N. Stoltz, P. Petroff, and J. Vuckovic, "Controlled phase shifts with a single quantum dot," *Science* **320**, 769–772 (2008).
3. A. Sipahigil, R. E. Evans, D. D. Sukachev, M. J. Burek, J. Borregaard, M. K. Bhaskar, C. T. Nguyen, J. L. Pacheco, H. A. Atikian, C. Meuwly *et al.*, "An integrated diamond nanophotonics platform for quantum-optical networks," *Science* **354**, 847–850 (2016).
4. R. E. Evans, M. K. Bhaskar, D. D. Sukachev, C. T. Nguyen, A. Sipahigil, M. J. Burek, B. Machielse, G. H. Zhang, A. S. Zibrov, E. Bielejec *et al.*, "Photon-mediated interactions between quantum emitters in a diamond nanocavity," *Science* **362**, 662–665 (2018).
5. A. E. Rugar, S. Aghaieimibodi, D. Riedel, C. Dory, H. Lu, P. J. McQuade, Z.-X. Shen, N. A. Melosh, and J. Vučković, "Quantum photonic interface for tin-vacancy centers in diamond," *Phys. Rev. X* **11**, 031021 (2021).
6. D. M. Lukin, M. A. Guidry, J. Yang, M. Ghezellou, S. D. Mishra, H. Abe, T. Ohshima, J. Ul-Hassan, and J. Vučković, "Optical superradiance of a pair of color centers in an integrated silicon-carbide-on-insulator microresonator," *arXiv preprint arXiv:2202.04845* (2022).
7. J. M. Kindem, A. Ruskuc, J. G. Bartholomew, J. Rochman, Y. Q. Huan, and A. Faraon, "Control and single-shot readout of an ion embedded in a nanophotonic cavity," *Nature* **580**, 201–204 (2020).
8. M. Lei, R. Fukumori, J. Rochman, B. Zhu, M. Endres, J. Choi, and A. Faraon, "Many-body cavity quantum electrodynamics with driven inhomogeneous emitters," *arXiv preprint arXiv:2208.04345* (2022).
9. D. M. Lukin, C. Dory, M. A. Guidry, K. Y. Yang, S. D. Mishra, R. Trivedi, M. Radulaski, S. Sun, D. Vercruysse, G. H. Ahn *et al.*, "4H-silicon-carbide-on-insulator for integrated quantum and nonlinear photonics," *Nat. Photonics* **14**, 330–334 (2020).
10. B.-S. Song, T. Asano, S. Jeon, H. Kim, C. Chen, D. D. Kang, and S. Noda, "Ultrahigh-q photonic crystal nanocavities based on 4h silicon carbide," *Optica* **6**, 991–995 (2019).
11. N. Jin, C. A. McLemore, D. Mason, J. P. Hendrie, Y. Luo, M. L. Kelleher, P. Kharel, F. Quinlan, S. A. Diddams, and P. T. Rakich, "Micro-fabricated mirrors with finesse exceeding one million," *Optica* **9**, 965–970 (2022).
12. D. M. Lukin, A. D. White, R. Trivedi, M. A. Guidry, N. Morioka, C. Babin, Ö. O. Soykal, J. Ul-Hassan, N. T. Son, T. Ohshima *et al.*, "Spectrally reconfigurable quantum emitters enabled by optimized fast modulation," *npj Quantum Inf.* **6**, 1–9 (2020).